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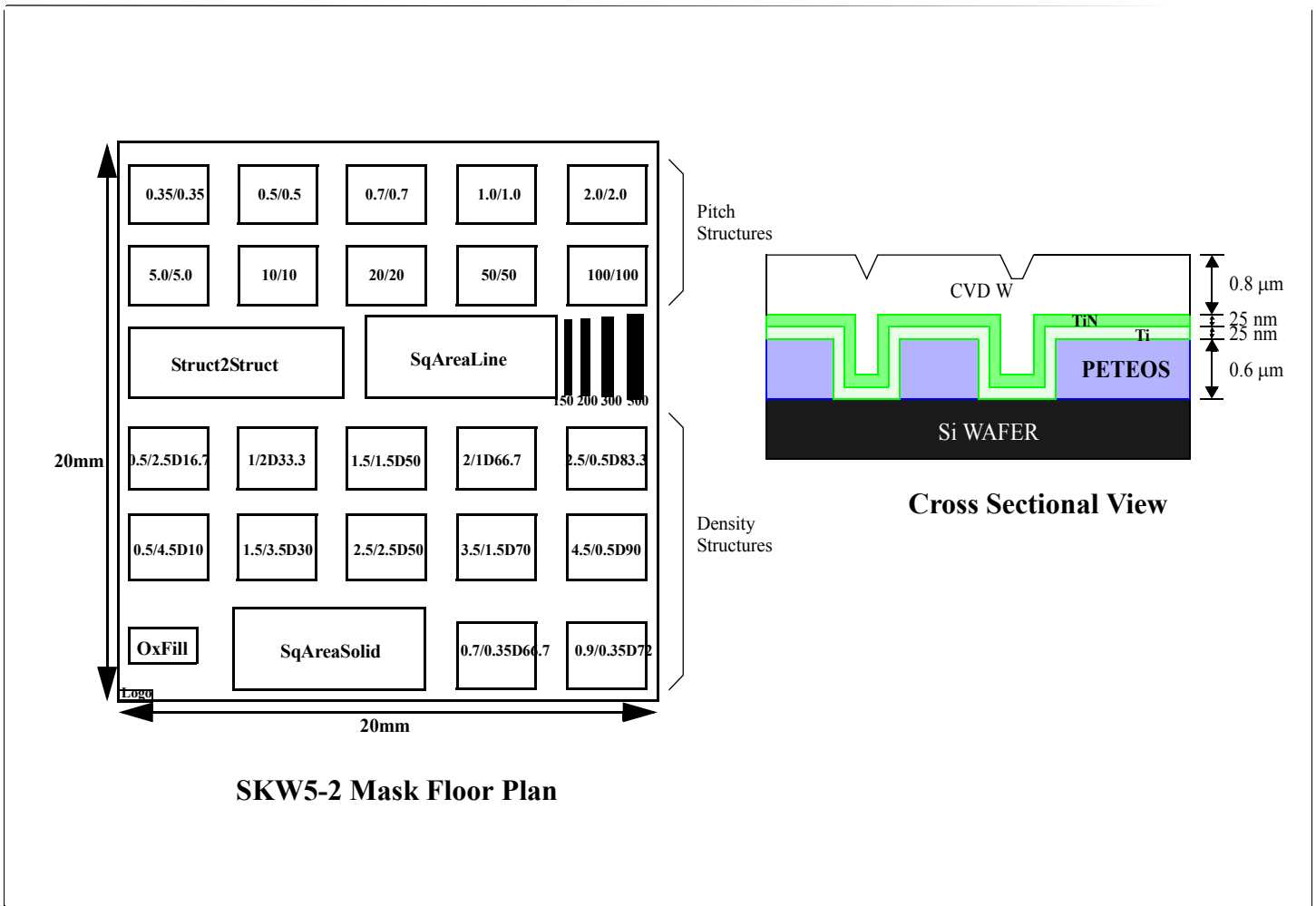
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SKW 5-2 Wafer Specifications

DATE: April 21, 2000



Oxide Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>PETEOS Thickness</i>		
Lot-to-Lot	6,000 Å	+/- 5 %
Within-Lot (Wafer-to-Wafer)		+/- 5 %
Within-Wafer		+/- 3 %
Within-Die		+/- 3 %

Ti Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>Ti PVD Film Thickness</i>		
Lot-to-Lot	250 Å	+/- 5 %
Within-Lot (Wafer-to-Wafer)		+/- 5 %
Within-Wafer		+/- 5 %
Within-Die		+/- 5 %

TiN Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>TiN PVD Film Thickness</i>		
Lot-to-Lot	250 Å	+/- 5 %
Within-Lot (Wafer-to-Wafer)		+/- 5 %
Within-Wafer		+/- 5 %
Within-Die		+/- 5 %

CVD W Film Deposition

PARAMETER	NOMINAL	TOLERANCE
<i>CVD W Film Thickness</i>		
Lot-to-Lot	8000 Å	+/- 10 %
Within-Lot (Wafer-to-Wafer)		+/- 10 %
Within-Wafer		+/- 5 %

Within-Die		+/- 5 %
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Patterning

PARAMETER	NOMINAL	TOLERANCE
<i>Patterning</i>		
Center Die X Location	-10.000 mm	+/- 100 μm
Center Die Y Location	-10.000 mm	+/- 100 μm
Die Size: X	20 mm	+/- 10 μm
Die Size: Y	20 mm	+/- 10 μm
Vertical Die Spacing	180 μm	+/- 10 %
Horizaontal Spacing	360 μm	+/- 10 %
<i>LineWidth Variation (measured on 2 μm structures)</i>		
Lot-to-Lot	2 μm	+/- 0.1 μm
Within-Lot (Wafer-to-Wafer)		+/- 0.1 μm
Within-Wafer		+/- 0.1 μm
Within-Die		+/- 0.1 μm